

Amplifier Transistor PNP Silicon

P2N2907A

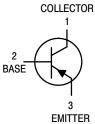
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	-60	Vdc
Collector-Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current — Continuous	I _C	-600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C P _D Derate above 25°C		1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

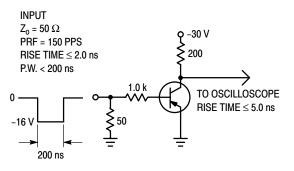
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ⁽¹⁾ (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-60	_	Vdc
Collector–Base Breakdown Voltage $(I_C = -10 \mu Adc, I_E = 0)$	V _{(BR)CBO}	-60	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	_	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	I _{CBO}	_ _	-0.01 -10	μAdc
Emitter Cutoff Current (V _{EB} = -3.0 Vdc)	I _{EBO}	_	-10	nAdc
llector Cutoff Current $V_{CE} = -10 \text{ V}$		_	-10	nAdc
Base Cutoff Current $(V_{CE} = -30 \text{ Vdc}, V_{EB(off)} = -0.5 \text{ Vdc})$	I _{BEX}	_	-50	nAdc

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic			Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C=-0.1 \text{ mAdc,}\\ &(I_C=-1.0 \text{ mAdc,}\\ &(I_C=-10 \text{ mAdc,}\\ &(I_C=-150 \text{ mAdc,}\\ &(I_C=-500 \text{ mAdc,}\\ \end{aligned} $	h _{FE}	75 100 100 100 50		_	
Collector–Emitter Solution ($I_C = -150 \text{ mAdc}$, ($I_C = -500 \text{ mAdc}$,	V _{CE(sat)}	_	-0.4 -1.6	Vdc	
Base–Emitter Saturation Voltage ⁽¹⁾ $(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$ $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$			_	-1.3 -2.6	Vdc
SMALL-SIGNAL	CHARACTERISTICS				
Current–Gain — Bandwidth Product ^{(1), (2)} (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		f _T	200	_	MHz
Output Capacitance (V _{CB} = -10 Vdc, I	C _{obo}	_	8.0	pF	
Input Capacitance ($V_{EB} = -2.0 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)			_	30	pF
SWITCHING CHA	RACTERISTICS	<u>, </u>			
Turn-On Time		t _{on}	_	50	ns
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$ $I_{B1} = -15 \text{ mAdc})$ (Figures 1 and 5)	t _d	_	10	ns
Rise Time		t _r	_	40	ns
Turn-Off Time		t _{off}	_	110	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, \\ I_{B1} = I_{B2} = -15 \text{ mAdc}) \text{ (Figure 2)}$	t _s	_	80	ns
Fall Time	181 - 187 - 19 HINGO) (Liguio 2)		_	30	ns

- 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.
- 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.





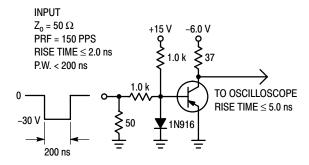


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

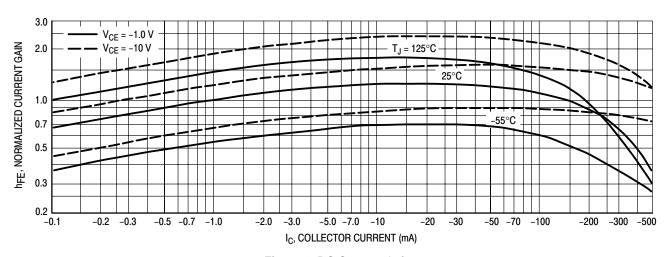


Figure 3. DC Current Gain

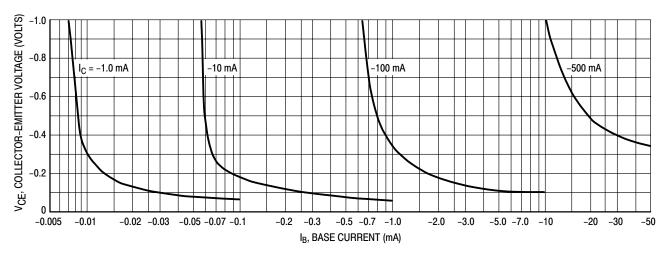


Figure 4. Collector Saturation Region

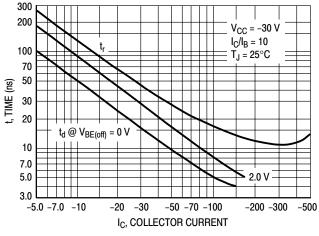


Figure 5. Turn-On Time

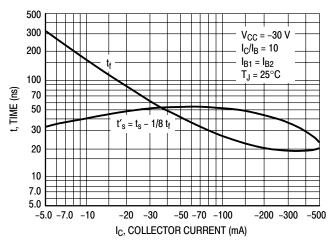


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

 $V_{CE} = 10 \text{ Vdc}, T_A = 25^{\circ}\text{C}$

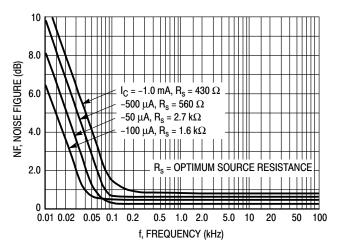


Figure 7. Frequency Effects

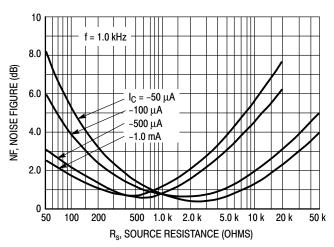


Figure 8. Source Resistance Effects

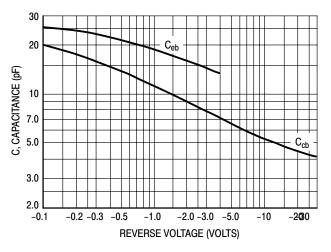


Figure 9. Capacitances

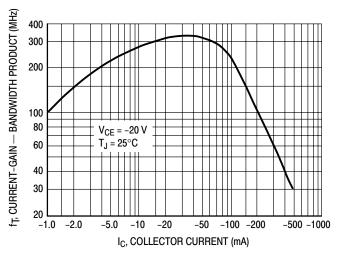


Figure 10. Current-Gain — Bandwidth Product

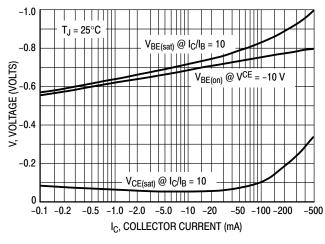


Figure 11. "On" Voltage

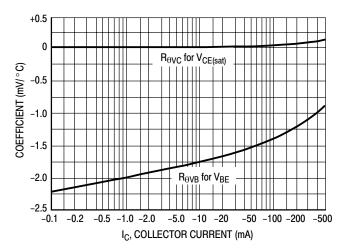
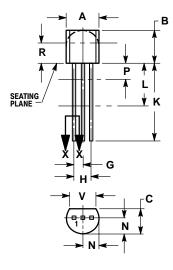


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

Notes

Notes

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